Docket No.

246179US90DIV

IN THE UNITED STATES PAT

IN RE APPLICATION OF:

Hiroyuki NAGASAWA, et al.

SERIAL NO: 10/734,221

GAU:

FILED:

December 15, 2003

EXAMINER:

DEMARK OFFICE

FOR:

COMPOUND CRYSTAL AND METHOD OF MANUFACTURING SAME

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

Applicant(s) wish to disclose the following information.

REFERENCES

The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are NOT attached, because they have been previously cited in parent application no. 10/140,187, filed
May 8, 2002.

☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present
application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s)
is attached along with PTO 1449.

☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

Each item of information contained in this information disclosure statement was first cited in any communication
from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of
this statement.

☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND, MAIER & NEUSTADT, P.C.

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Form PTO 1449 U.S. DEPARTMENT OF COMMENCE			246179US90DIV	10/734,221					
		THAUL		APPLICANT					
		RENCES CITED BY AP	PLICANT	Hiroyuki NAGASAWA, et al.					
				FILING DATE		GROUP			
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				U.S. PATENT DOCUMENTS					
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS		NG DATE	
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*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.